

TMR2701

High Sensitivity and Low Hysteresis TMR linear sensor

General Description

The TMR2701 linear sensor utilizes a unique push-pull Wheatstone bridge composed of four unshielded TMR sensor elements. The unique bridge design provides a high sensitivity differential output that is linearly proportional to a magnetic field applied parallel to the surface of the sensor package, and it provides superior temperature compensation of the output. The TMR2701 is available a 6mm X 5mm X 1.5mm SOP8 package.

Features and Benefits

- Tunneling Magneto resistance (TMR) Technology
- High Sensitivity
- Large Dynamic Range
- Very Low Power Consumption
- Excellent Thermal Stability
- Very Low Hysteresis
- Compatible with wide Range of Supply Voltages

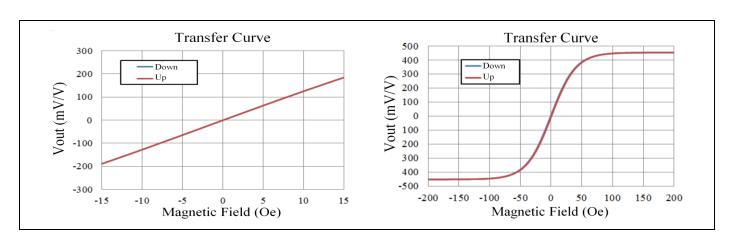
Applications

- Weak Magnetic Field Sensing
- Current Sensors
- Position and Displacement Sensing



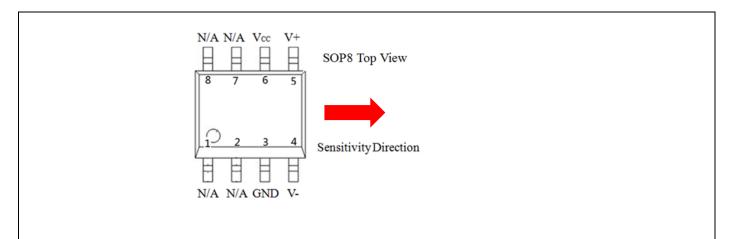
Transfer Curve

The following figure shows the response of the TMR2701 to an applied magnetic field in the range of ±15 Oe and ±200 Oe when the TMR2701 is biased at 1V.



Pin Configuration

(Arrow indicates direction of applied field that generates a positive output voltage.)



Pin No.	Pin Name Pin Function			
1,2,7,8	N/A	Not connected		
3	GND	Ground		
4	V-	Analog Differential Output 2		
5	V+	Analog Differential Output 1		
6	V_{cc}	Supply Voltage		

Absolute Maximum Ratings

Parameter	Symbol	Limit	Unit	
Supply Voltage	V_{CC}	7	V	
Reverse Supply Voltage	V_{RCC}	7	V	
Max Exposed Field	H _E	4000	Oe ⁽¹⁾	
ESD Voltage	V_{ESD}	4000	V	
Operating Temperature	T _A	-40~125	°C	
Storage Temperature	T _{stg}	-50 ~150	°C	

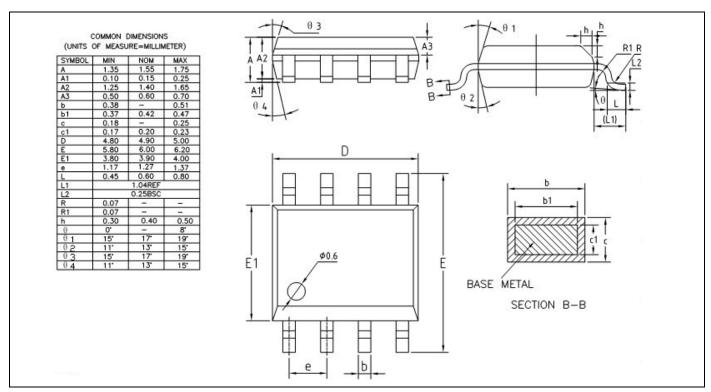
Specification (V_{CC}=1.0V, T_A=25°C, Differential Output)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Supply Voltage	Vcc	Operating		1	7	V
Supply Current	Icc	Output Open		12.5		μA
Resistance	R			80 ⁽²⁾		KOhm
Sensitivity	SEN	Fit @ ±15 Oe		12		mV/V/Oe
Saturation Field	H _{sat}			±50		Oe
Non-Linearity	NONL	Fit @ ±15 Oe		1		%FS
Offset Voltage	V _{offset}		-30		30	mV/V
Hysteresis	Hys	Fit @ ±15 Oe		0.3		Oe
Temperature Coefficient of	TCR	H = 0 Oe		0.01		mV/V/°C
Resistance						111V/V/ C
Temperature Coefficient of	TCS			-1000		PPM/°C
Sensitivity						

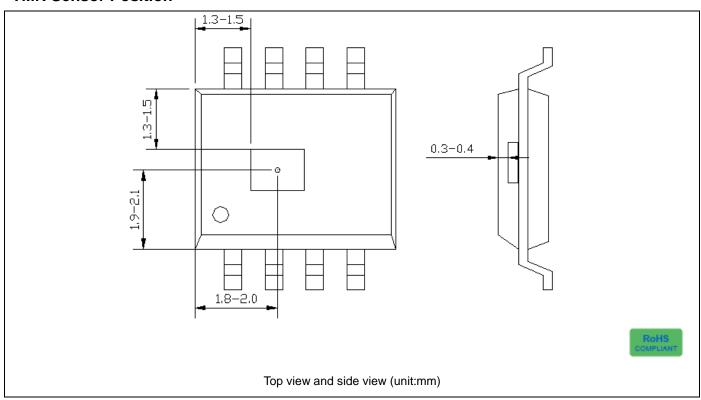
Notes:

(1) 1 Oe (Oersted) = 1 Gauss in air = 0.1 millitesla = 79.8 A/m.

Package Information



TMR Sensor Position







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